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## AN EXPERIMENTAL STUDY OF THE MOBILITY OF

 EDGE DISLOCATIONS IN PURE COPPER SINGLE CRYSTALSK. M. Jassby and T. Vreeland, Jr.<br>W. M. Keck Laboratories, California Institute of Technology Pasadena, California

## ABSTRACT

The velocity of selectively-introduced edge dislocations in 99.999 percent pure copper crystals has been measured as a function of stress at temperatures from $66^{\circ} \mathrm{K}$ to $373^{\circ} \mathrm{K}$ by means of a torsion technique. The range of resolved shear stress was 0 to 15 megadynes $/ \mathrm{cm}^{2}$ for seven temperatures $\left(66^{\circ} \mathrm{K}, 74^{\circ} \mathrm{K}, 83^{\circ} \mathrm{K}, 123^{\circ} \mathrm{K}, 173^{\circ} \mathrm{K}\right.$, $\left.296^{\circ} \mathrm{K}, 373^{\circ} \mathrm{K}\right)$.

Dislocation mobility is characterized by two distinct features;
(a) relatively high velocity at low stress (maximum velocities of about $9000 \mathrm{~cm} / \mathrm{sec}$ were realized at low temperatures), and (b) increasing velocity with decreasing temperature at constant stress.

The relation between dislocation velocity and resolved shear stress is:

$$
\mathrm{v}=\mathrm{v}_{\mathrm{o}}\left(\frac{{ }^{\tau} \mathrm{r}}{\tau_{\mathrm{o}}}\right)^{\mathrm{n}}
$$

where $v$ is the dislocation velocity at resolved shear stress $\tau_{r}, V_{0}$ is a constant velocity chosen equal to $2000 \mathrm{~cm} / \mathrm{sec}, \tau_{0}$ is the resolved
shear stress required to maintain velocity $\mathrm{v}_{\mathrm{o}}$, and n is the mobility coefficient. The experimental results indicate that $\tau_{0}$ decreases from $16.3 \times 10^{6}$ to $3.3 \times 10^{6}$ dynes $/ \mathrm{cm}^{2}$ and $n$ increases from about 0.9 to 1.1 as the temperature is lowered from $296^{\circ} \mathrm{K}$ to $66^{\circ} \mathrm{K}$.

The experimental dislocation behavior is consistent with an interpretation on the basis of phonon drag. However, the complete temperature dependence of dislocation mobility could not be closely approximated by the predictions of one or a combination of mechanisms.

## 1. INTRODUCTION

The experimental study of dislocation mobility in single crystals has advanced along two distinct paths, those of the so-called direct and indirect measurements. Historically, the latter preceded the former by about a decade, during which time the quality of single crystals was greatly improved and techniques were developed for observing individual dislocations.

Indirect experiments (which employ macroscopic measurements only) invariably require a dislocation model for the interpretation of measurements, and herein lies the disadvantage of the method, for each model employs presuppositions which can only be affirmed by microscopic observations. Of course, no such restraints are imposed on direct measurements, but the experimental techniques here are generally more difficult to realize.

As far as copper is concerned, mobility studies have been made by both methods (Alers and Thompson 1961, Stern and Granato 1962, Suzuki et al. 1964, Marukawa 1967, Greenman et al. 1967), and there is general agreement only on the order of magnitude of dislocation damping at room temperature. In this paper, the results of further direct mobility measurements in copper are presented. The work comprised a study of the interaction of individual dislocations with the crystal lattice.

The basic testing apparatus was a torsion machine developed by Pope, et al. (1964) and used successfully by them for mobility measurements in zinc (1967) and later by Gorman, et al. (1969) for work in aluminum. The experimental procedure used here follows essentially their original work.

## 2. EXPERIMENTAL TECHNIQUES

In this section, the techniques used for obtaining the dislocation velocity-shear stress measurements are discussed. The experimental procedure can be outlined as follows:

1. A copper single crystal is electrolytically machined into a right circular cylinder with the cylindrical axis in the [111] direction.
2. One end surface is scratched with an $A l_{2} \mathrm{O}_{3}$ whisker to produce dislocations on slip planes parallel to the end surface and about 1 micron below it.
3. The positions of these dislocations are determined from Berg-Barrett x-ray micrographs.
4. The scratched surface of the test crystal is bonded to the torsion apparatus, whereupon a torsional stress pulse is applied to the crystal.
5. The positions of displaced dislocations are established from Berg-Barrett x-ray micrographs.

## Test Specimens

Copper single crystals with an orientation near the [ 11111$]$ pole were grown from 99.999 percent pure material by a modified Bridgman technique, similar to that developed by Young and Savage (1964). The parent crystals were acid-sliced perpendicular to the growth direction to obtain cylinders 1 cm long and 2.5 cm in diameter. Each cylinder was then electrolytically machined to provide a single circular test specimen 1.33 cm in diameter, about 0.9 cm long, and
with a cylindrical axis within $0.25^{\circ}$ of the [ $\left.\begin{array}{lll}1 & 1 & 1\end{array}\right]$ pole.
The test crystals were annealed for 1 to 7 days at $1040^{\circ} \mathrm{C}$ in a purified argon atmosphere of 1 psig , and the end surfaces were then lightly electropolished to remove traces of evaporation pits.

Etching the (111) end surfaces of annealed crystals with Livingston's etch (1960) revealed between $10^{3}$ to $10^{5}$ dislocation intersections per $\mathrm{cm}^{2}$. In addition, the crystals were generally free from substructure.

One end surface of each crystal was scratched with an $\mathrm{Al}_{2} \mathrm{O}_{3}$ whisker parallel to the three $\langle 110\rangle$ directions in that surface. The scratching apparatus is well described by Pope (1967). The character of the dislocations produced by the scratching procedure is discussed later.

## The Berg-Barrett X-Ray Diffraction Technique

Dislocations on (111) planes less than 2 microns from an end surface of a test specimen were observed by the Berg-Barrett technique, as described by Turner, et al. (1968). Characteristic Co radiation diffracted from a set of $\{220\}$ planes provided an image of the near surface of the test crystal on a high-resolution $x$-ray plate. A pure iron filter, 0.0013 cm thick, absorbed fluorescent radiation. Dislocation Burgers vectors were identified by noting that when the reciprocal lattice vector of the set of diffracting planes was perpendicular to the Burgers vector of a dislocation, the image of that dislocation was nearly extinct. Hence, by obtaining diffraction micrographs from any two of the three available sets of $\{220\}$ planes, all Burgers vectors in (111) planes could be identified.

## The Character of the Selectively-Introduced Dislocations

A typical scratch in a $\langle 110\rangle$ direction produced dislocations on (111) planes with Burgers vectors in either of the two remaining $\langle 110\rangle$ directions (Fig. 1a). In addition, dislocations were created on the three $\{111\}$ cross slip planes (Fig. 1b). Etch pits formed where the ends of dislocations on the primary (111) planes crossslipped to the free surface of the crystal. Dislocations on the primary (111) planes were commonly 0.01 to 0.02 cm in length. The Torsional Apparatus and Torsion Test

The torsion machine developed by Pope, et al. (1964) was slightly modified to accommodate copper test specimens. Steel torsion rods, 1.27 cm in diameter, were used in place of the usual titanium rods. A polycrystalline copper rod was acoustically matched to the steel for elastic torsional waves. Semiconductor strain gages were attached to the copper rod 1.9 cm from its lower end, as shown schematically in Fig. 2.

The test specimen, with a cylindrical diameter identical to that of the gage bar, was mounted as shown in Fig. 2. A copper extension rod was used in the earlier tests to afford longer stress pulse times, but proved superfluous and its use was discontinued.

The test procedure essentially duplicated that employed by Gorman et al. (1969), although the range of their test temperatures was slightly narrower. The bonding agents are listed in Table 1.

(a)

(b)

Fig. 1 Typical Scratch Segment Before Testing. (a) Dislocations on Primary Slip Planes with Burgers Vectors $\underline{b}_{1}$ and $\underline{b}_{2}$, (b) the Same Area as in (a) but Etched to Reveal Forest Dislocations.


Fig. 2 Schematic Diagram of Lower End of Torsion Machine.

## TABLE 1. Agents Used to Bond the Test Crystals to the Torsion Machine

| Test <br> Temperature <br> $\left({ }^{\circ} \mathrm{K}\right)$ | Bonding Agent | Volumetric <br> Ratio |
| :--- | :--- | :--- |
| 373 | commercial sugar | - |
| 296 | quartz-type wa | - |
| 173 | glycerine-ethanol | $3: 2$ |
| 123 | glycerine-ethanol | $1: 5$ |
| 83 | isopentane-methylcyclohexane | $3: 1$ |
| 74 | isopentane-methylcyclohexane | $10: 1$ |
| 66 | isopentane-3-methylpentane | $10: 1$ |

Two or more tests were made at each temperature. The time between scratching a crystal and torsion testing never exceeded 48 hours. A delay of more than four days produced a measurable decrease in dislocation mobility.

## 3. EXPERIMENTAL RESULTS

## Torsional Stresses in the Test Crystal and the Resolved Shear

## Stress on Dislocations

The oscilloscope trace of the strain gage output (torque record) for a typical torsion test is found in Fig. 3a. In this case, the test crystal is 0.9 cm long and the thickness of the bonding agent (quartz-type sticky wax) is 0.003 cm . While the strain gages provide only a record of the torque in the copper gage bar, it is possible to extrapolate the results to the surface of the copper crystal with knowledge of the elastic properties of the bonding agent and the response of the copper specimen to an incident torsional wave. The former can be well-defined experimentally, but less can be inferred about the behavior of the test crystal. One should refer to Appendices $A$ and $B$ for discussion of these points. The torque record at the test crystal surface is plotted in Fig. 3b.

The shear stress on the (111) surface of the test crystal at time $t$ at a radius $r$ from the cylindrical axis of the crystal is:

$$
\begin{equation*}
\tau(r, t)=\frac{M(t) r}{I} \tag{3.1}
\end{equation*}
$$

where $M(t)$ is the torque at the surface at time $t$, and I is the polar moment of inertia of the crystal.

Torsional stresses exert glide forces on dislocations lying on the cross-slip $\{111\}$ planes as well as those of the primary (111) system. The resolved shear stress on a dislocation on a primary slip


Fig. 3. Typical Torque vs. Time Record for Torsion Test.
(a) at Strain Gages, (b) Calculated Pulse at Test Crystal Surface.
plane is:

$$
\begin{equation*}
\tau_{r}(r, t)=0.866 \tau(r, t)=\frac{0.866}{I} M(t) r \tag{3.2}
\end{equation*}
$$

near its originating scratch, while the resolved shear stress on a dislocation of a cross-slip system is $\leq \frac{1}{3} \tau_{r}(r, t)$, depending on the orientation of its Burgers vector.

Dislocation Displacements and the Measurement of Dislocation Mobility

Figures 4 a and 4 b display the same scratched area of a test crystal preceding and following the torsion test. The region has been etched in Fig. 4c to delineate the intersection of forest dislocations with the primary glide system. Etch pits indicate where ends of dislocations on the primary glide planes have cross-slipped to the surface. These cross-slipped segments appear to have constrained the main body of the dislocation to glide in a direction parallel to its Burgers vector when the torsion stress was applied.

The displacements of the farthest moving dislocations lying in the edge orientation after testing were measured as a function of the radius $r$. These results are cataloged in Fig. 5. Displacement measurements are given only for those tests which provided data over a wide range of radius. From Fig. 5 we observe that:

$$
\begin{equation*}
d(r)=K r^{n} \tag{3.3}
\end{equation*}
$$

where $d(r)$ is the maximum dislocation displacement at radius $r$, and K and n are experimentally determined. If $\mathrm{v}(\mathrm{r}, \mathrm{t})$ is the dislocation velocity at radius $r$ at time $t$, then:




Figure 5. Dislocation Displacement as a Function of Distance $r$ from the Cylindrical Axis of the Test Crystal (for Two Temperatures).

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Cylindrical Axis of the Test Crystal (for Two Temperatures).


Figure 5. Dislocation Displacement as a Function of Distance $r$ from the Cylindrical Axis of the Test Crystal.
(continued)

$$
\begin{equation*}
\int_{0}^{T} \mathrm{v}(\mathrm{r}, \mathrm{t}) \mathrm{dt}=\mathrm{Kr} \mathrm{r}^{\mathrm{n}} \tag{3.4}
\end{equation*}
$$

where $T$ is the stress pulse duration. The relation between dislocation velocity and shear stress is postulated to be:

$$
\begin{equation*}
v(r, t)=v_{o}\left(\frac{\tau_{r}(r, t)}{\tau_{o}}\right)^{m} \tag{3.5}
\end{equation*}
$$

where $\tau_{0}$ and $m$ are functions of temperature and $v_{0}$ is chosen such that $v(r, t)$ equals $2000 \mathrm{~cm} / \mathrm{sec}$ when $\tau_{r}(r, t)$ equals $\tau_{o}$. Then from equation (3.2):

$$
\begin{equation*}
\mathrm{v}(\mathrm{r}, \mathrm{t})=\mathrm{v}_{\mathrm{o}}\left(\frac{0.866 \mathrm{M}(\mathrm{t})}{\mathrm{I}_{\mathrm{T}}}\right)^{\mathrm{m}} \mathrm{r}^{\mathrm{m}} \tag{3.6}
\end{equation*}
$$

Substitution of $\mathrm{v}(\mathrm{r}, \mathrm{t})$ into equation (3.4) gives:

$$
\begin{align*}
& m=n  \tag{3.7}\\
& \frac{l}{\tau_{o}}=\left(\frac{I}{0.866} ;\left(\frac{K}{v \int_{0}^{T} M^{n}(t) d t}\right)^{\frac{1}{n}} .\right.
\end{align*}
$$

Hence, n is a function of temperature only, while K depends on temperature and the magnitude and duration of the stress pulse. With reference to equation (3.3) and Fig. 5, it is recognized that $n$ is given by the slope of the "best-fit" straight line through the experimental points, while K is determined from the straight line intercept. $\tau_{0}$ is found from equation (3.7) upon integration of the torque function $M^{n}(t)$. The values of $n$ and $\tau_{o}$ are presented in Table II, and the velocity-stress relation is plotted in Fig. 6.


Fig. 6 Dislocation Velocity as a Function of Resolved Shear Stress for the Range of Stressess Used at Euch Trat Tr-mprature.

## The Dislocation Damping Coefficient

If dislocation velocity is directly proportional to the resolved shear stress, it is possible to write:

$$
\begin{equation*}
\mathrm{Bv}=\tau_{\mathrm{r}} \mathrm{~b}, \tag{3.8}
\end{equation*}
$$

where $B$ is the damping coefficient and $b$ is the magnitude of the dislocation Burgers vector. With a presupposed mobility coefficient equal to 1 , the data of Fig. 5 may be interpreted by drawing 'bestfit" lines of unit slope through the experimental points. Then a comparison of equations (3.7) and (3.8) provides:

$$
\begin{equation*}
B=\frac{0.866 b}{K I} \int_{0}^{T} M(t) d t \tag{3.9}
\end{equation*}
$$

The linearized results are shown in Table III and Fig. 7.

Table II. Experimentally Determined Values of the Mobility Coefficient, $n$, and the Resolved Shear Stress, $\tau_{0}$,
Required to Maintain a Dislocation Velocity of $2000 \mathrm{~cm} / \mathrm{sec}$.
Temperature
Mobility Coefficient, $n$ $10^{6} \stackrel{\text { To }}{\text { dynes } / \mathrm{cm}^{2}}$

373
1.00
13.0

296
0.88
16.3

173
1.00
9.5

123
$1.03 \quad 5.8$
83
1.12
4.0

74
1.14
3.6

66
1.10
3.3


Fig. 7 Dislocation Damping Coefficient for Edge Dislocations in Copper Single Crystals as a Function of Temperature (from Linearized Measurements).

Table III. Values of the Dislocation Damping Coefficient B, and $\tau_{0}$, Found by Assuming a Mobility Coefficient Equal to 1.

| Temperature ${ }^{\circ} \mathrm{K}$ | Mobility Coefficient, B $10^{-4}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ | $10^{6}$ dynes $/ \mathrm{cm}^{2}$ |
| :---: | :---: | :---: |
| 373 | 1.67 | 13.0 |
| 296 | 1.70 | 13.4 |
| 173 | 1.20 | 9.5 |
| 123 | 0.73 | 5.7 |
| 83 | 0.60 | 4.7 |
| 74 | 0.47 | 3.7 |
| 66 | 0.36 | 2.8 |

## 4. DISCUSSION OF RESULTS

Several points must be considered in the interpretation of the experimental results. In light of the uncertainty in the actual stress state in the crystal (Appendix B), we discuss the validity of the observed temperature dependence of the mobility coefficient. Use of equation (3.5) implies that dislocation velocity is in phase with the resolved shear stress and we argue that dislocation acceleration times are negligible in the velocity region considered. It is recognized that a dislocation on a primary slip plane glides with its ends on the appropriate cross-slip planes for which the resolved shear stress is considerably reduced. This source of drag is considered. With forest dislocation densities as high as $10^{5} \mathrm{etch}$ pits/ $\mathrm{cm}^{2}$, and dislocation displacements of nearly 0.1 cm in some cases, intersection mechanisms cannot be neglected. The drag due to forest
dislocations is discussed. Finally, the present results are compared with previously published work.

Effect of the Uncertainty in the Stress State on the Measurement of the Mobility Coefficient

In Appendix B, it was found that the elastic inhomogeneity of the test crystal causes an increase of the tangential shear stress with respect to the pure torsional value for the inner region of the crystal and produces the opposite effect near the outer boundary [equation (B-29)]. The net effect is to underestimate the value of the mobility exponent by a small amount. One must also consider the radial shear stresses on the crystal surface required to establish a state of equilibrium. In the limit these could be as large as the deviation of the tangential shear stresses from their pure torsion values. Their effect on dislocation mobility will be different for different Burgers vectors (Fig. 1), but must be small relative to the changes in the tangential shear stresses because their resolving factor on the dislocations is 0.5 rather than 0.866 .

In conclusion, one can safely assume that the temperature dependence of the mobility coefficient observed experimentally is indeed a real effect and is somewhat underemphasized by the state of stress in the crystal.

## Dislocation Acceleration Time

Gorman et al (1969) discussed the acceleration times for a straight dislocation using a mobility coefficient equal to 1 . They found an acceleration time constant for aluminum equal to about $10^{-11}$ seconds. A similar result holds for copper, and it can safely
be assumed that dislocation velocity is in phase with applied stress for the velocity range and mobility coefficients found experimentally. Breakaway of a Dislocation from a Scratch and Its Motion on a Primary (111) Glide Plane

X-ray micrographs revealed that screw components of dislocations on the primary glide system cross-slipped quite readily to the free surface. With the aid of anisotropic elasticity, the free surface attractive stress on the cross-slip plane of a screw dislocation 1 micron below the free surface was estimated to be about $10^{7}$ dynes $/ \mathrm{cm}^{2}$. Since dislocations in copper are extremely mobile at this stress, it is recognized quite readily that any dislocation which assumes a screw orientation will rapidly cross-slip to the free surface. Fig. 4 suggests that the primary glide dislocation semi-loops did not expand when motion was induced by the torsional stresses, but rather remained of similar length. This is easily understood if it is assumed that the semi-loops increased in radius until both ends assumed screw configurations, whereupon crossslip occurred and the dislocations were free to glide through the lattice, with their ends extending to the free surface.

Figure 8 is a schematic representation of an edge dislocation $B C$ on a primary slip plane gliding with velocity v through the crystal lattice. Crystal geometry requires that the applied torsional stress, resolved on the cross-slip plane, act on the segment $C D$ in the direction of motion, while in the opposite direction on AB.

Each of $A B$ and $C D$ constitutes a dragging force on the edge dislocation. The magnitude of these forces was considered by

Jassby (1969) who showed how they can lead to overestimation of the lattice friction force. The overestimation was found to be negligible for edge dislocations of length greater than 0.01 cm .

Intersection of the Dislocation Forest by Dislocations on the Primary (111) Glide Planes

Maximum dislocation displacements on the primary slip system were about 0.1 cm . The motion of dislocations on other slip systems was considerably less because of their much smaller resolved shear stresses. This implies that the forest dislocations produced in the scratching process (Fig. lb) remained near the scratches during the torsion test. This, of course, is verified in Fig. 4c. However, if a dislocation forest density of $10^{5}$ intersections $/ \mathrm{cm}^{2}$ is considered, then a dislocation 0.01 cm in length traveling 0.1 cm on a primary (111) plane experiences, on the average, 100 intersections with the grown-in forest. The number of intersections is decreased by one order of magnitude for each tenfold decrease in forest density.

The experimental techniques presently available can be employed to estimate rather closely the number of forest intersections suffered by each mobile dislocation (Fig. 4c), but generally they were not used for this purpose. No correlation was made between the number of dislocation intersections and dislocation mobility. Instead, Saada's calculation of the stresses required to overcome attractive and repulsive interactions was used. For a randomly distributed forest, Saada (1962) estimated that this


$$
\begin{aligned}
& F_{A B}=\frac{1}{3} \tau_{r} b+B v_{n} \\
& F_{B C}=\tau_{r} b-B v_{n} \\
& F_{C D}=-\frac{1}{3} \tau_{r} b+B v_{n}
\end{aligned}
$$

Figure 8. $\begin{aligned} & \text { Schematic Representation of a Dislocation } \\ & \text { Gliding on a Primary Slip Plane Under the }\end{aligned}$ Gliding on a Primsional Stresses. FAB, F BC, and FCD are the Normal Forces per Unit Length Acting on the Three Segment of the Dislocation. b is the Dislocate Stress on vector, $T_{r}$ is the Re $h$ is the Distance from the Segment BC , and
the Primary Slip Plane to the Free Surface.
stress, $\tau$, is given by:

$$
\begin{equation*}
\tau=\frac{\mu_{0} b}{\alpha l}, \tag{4.1}
\end{equation*}
$$

where $\alpha$ is 2.5 for attractive interactions and 10 for repulsive interactions, $\mu_{o}$ is the appropriate isotropic shear modulus, b is the magnitude of the dislocation Burgers vector, and $\ell$ is the distance between forest trees. In Table 4 are found the largest possible back stress (attractive interactions) in copper for forest densities of $10^{3}, 10^{4}, 10^{5}$, and $10^{6}$ intersections $/ \mathrm{cm}^{2}$. All of the dislocation displacement measurements in Fig. 5 were from dislocations with resolved shear stresses between the limits of $10^{6}$ and about $1.7 \times 10^{7}$ dynes $/ \mathrm{cm}^{2}$. Hence, according to Saada's calculation, back stresses may be significant in those regions of the test crystals where forest densities exceed about $10^{4}$ intersections $/ \mathrm{cm}^{2}$. These results, then, predict scatter in the mobility behavior between regions with different forest densities. In the test crystals used, there were an adequate number of areas where dislocation motion on a primary ( 111 ) plane was unaffected by the dislocation forest. This, of course, provides justification for choosing "best-fit" curves through the points of greatest velocity in Fig. 5.

## Comparison of Results with Earlier Experiments

Early estimates of the lattice friction force in pure copper single crystals were deduced from internal friction measurements. These measurements were interpreted on the basis of the string model of a vibrating dislocation (Granato and Lücke 1956).

Alers and Thompson (1961) reported the first indirect measurements of the damping coefficient in copper. Their experimental measurements were in fair agreement with the predictions of the simple string model. Interestingly, they found that B decreased by about a factor of 4 between room temperature and $60^{\circ} \mathrm{K}$, a result similar to the deductions of our work. They estimated the room temperature value of $B$ to be about $10^{-4}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ from the frequency at the maximum decrement and $8 \times 10^{-4}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ using the measured temperature dependence of the decrement at constant frequency.

Stern and Granato (1962) refined the simple theory by considering the vibrating dislocations to be of two distinct types, edge and screw, with significantly different line tensions. They postulated that each dislocation type obeyed the Granato-Lücke theory and was pinned with an exponential distribution of loop lengths. The damping coefficient was assumed to be the same for both edge and screw dislocations. On this basis, Stern and Granato successfully predicted the effects of temperature and neutron irradiation on the energy decrement. They concluded that $\mathrm{B} \leq 6.5 \times 10^{-4}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ at room temperature.

Suzuki et al. (1964) used the asymptotic behavior of the decrement to obtain B from their measurements on two crystals. They found B equal to $2.7 \times 10^{-5}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ for one crystal and $1.2 \times 10^{-5}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$ for the second, both at room temperature. It appears that their measurements were all taken near the rather broad maximums of the decrements (Figs. 3 and 4 of Suzuki et al.), and thus rather gross extrapolation was required to obtain B.

The broad maxima in decrement vs. frequency suggest an interpretation on the basis of the more refined model put forward by Stern and Granato (1962).

Marukawa (1967) directly measured dislocation mobility in pure copper at room temperature by applying stress pulses to single crystals in a 4 -point bending jig. A similar etching technique was used by Greenman, et al. (1967) for measurements in single crystals subjected to torsional stress pulses. While Marukawa's measure ments were taken from grown-in dislocations, Greenman, et al. introduced dislocations into the test crystals with a scratching apparatus.

Marukawa found a mobility coefficient of 2. It is difficult to make a realistic appraisal of the lattice damping from his results because the extent of the segregation of impurities and lattice defects to his dislocations and their corresponding effects on dislocation motion are unknown, as is the extent of interaction with other dislocations. Also, Marukawa conducted his tests over a limited range of resolved shear stress $\left(0.5 \times 10^{6}\right.$ to $3 \times 10^{6}$ dynes $\left./ \mathrm{cm}^{2}\right)$, which makes his determination of the mobility coefficient relatively inaccurate.

Greenman, et al. were burdened by the problem of grown-in dislocations only with reference to their influence on the motion of freshly introduced dislocations. For resolved shear stresses from about $2 \times 10^{6}$ to $2 \times 10^{7}$ dynes $/ \mathrm{cm}^{2}$, they reported a mobility coefficient of 0.7 at room temperature. They then linearized their
measurements by choosing $n=1$ and determined a damping coefficient equal to $7 \times 10^{-4}$ dynes $\mathrm{sec} / \mathrm{cm}^{2}$. It is recalled that Greenman, et al. used average dislocation displacements rather than maximum displacements to obtain their results, and we now realize that this significantly overestimates the magnitude of $B$. It must also be remembered that there is uncertainty as to the character of their mobile dislocations, although they were probably near the $30^{\circ}$ mixed type.

The results of Greenman, et al. and those presented in this thesis indicate that the mobility coefficient at room temperature is slightly smaller than 1 , most probably between the limits of 0.7 and 0.9 for both edge and mixed dislocations. The indirect measurements provide the correct order of magnitude of damping in copper, but of course cannot give a measure of the mobility coefficient. The results of Alers and Thompson are encouraging in view of their prediction of the temperature dependence of $B$. The results of Stern and Granato and Suzuki, et al. suggest that, in the general case, the complexity of dislocation configurations in the test crystals precludes an interpretation by the simple model.

## Dislocation-Phonon Interactions

Dislocation mobility in pure copper single crystals as well as in zinc (Pope and Vreeland 1969) and aluminum (Gorman et al. 1969) is characterized by two important features: (a) the attainment of relatively high velocities for small applied stresses, and (b) decreasing interaction with the crystal lattice with decreasing temperature in the temperature range from about $70^{\circ} \mathrm{K}$ to $300^{\circ} \mathrm{K}$. This
dislocation behavior was first proposed theoretically by Leibfried (1950), nearly twenty years before direct experimental evidence was available. His model postulated that, in the absence of a large Peierls' barrier, dislocation motion was damped by the interaction of lattice thermal waves with the elastic properties of dislocations. Leibfried specifically considered how dislocation mobility is affected by the stress field of a thermal phonon. This, however, is not the only mechanism to be considered. Since 1950, theories have been put forward to explain thermal phonon-dislocation core and thermal phonon-dislocation strain field interactions. The inherent complexity of the problem has required that many simplifying assumptions be made to obtain estimates of the dislocation drag coefficient as a closed form function of lattice and dislocation properties. While the various theories predict the proper order of magnitude of damping in copper, the experimentally observed temperature dependence of the damping coefficient of edge dislocations in the temperature range from $66^{\circ} \mathrm{K}$ to $373^{\circ} \mathrm{K}$ could not be closely approximated by the predictions of one or combination of mechanisms.

The phonon viscosity theory developed by Mason and others is attractive because it alone predicts the high-temperature behavior (temperatures near the Debye temperature) of the damping coefficient that is experimentally observed. However, the theory has not been worked out in great detail, and there exists some confusion as to the validity of several of its arguments. In a subsequent paper we will consider this theory in more detail as it applies to FCC crystals. The theory itself stems from the original work of Akhieser,
(1939) who considered the lattice absorption of energy from acoustic (or strain) waves with long wave-lengths relative to the thermal phonon mean free path. He reasoned as follows: the thermal phonons are highly localized with respect to the varying strain field; hence, they can be considered as traveling through a uniform medium with a slowly modulating strain field. The lattice thermal frequencies are changed as the result of the impression of the strain, creating temperature differences between phonon modes at any spatial point. The phonons relax to a new thermal equilibrium at some common temperature (adiabatic temperature) through phonon-phonon collisions. Akhieser considered 3-phonon N-processes due to anharmonic lattice terms and showed, using the Debye approximation for phonon wave velocities, that the relaxation process was accompanied by an increase of entropy of the system and a corresponding energy absorption from the strain wave.

If the strain perturbation is spatially - dependent, the temperature change of each phonon mode is a function of position in the crystal. Hence, in the general case, the common equilibrium temperature of the relaxed phonons depends on position in the crystal. This is the so-called adiabatic state (Biot 1956, Lücke 1956). Return to the isothermal condition is now determined by the macroscopic parameters involved in heat flow between spatial points. The energy absorbed from a dislocation strain field in the adiabatic-isothermal transition has been determined exactly (Eshelby 1949, Weiner 1958) and is negligibly small for metals.

In a series of papers, Mason (1960, 1964), Mason and Bateman
(1964), and Mason and Rosenberg (1967) considered the initial phonon transition and showed that the Akhieser effect was applicable to the absorption of energy from the strain field of a dislocation traveling through an otherwise defect-free crystal lattice. Rather than calculate the entropy produced during the relaxation process described above, they postulated that the elastic stiffnesses of the crystal were altered by the perturbation from equilibrium. They noted that a change in an elastic stiffness multiplied by the time required for the material relaxation was equal to a viscosity, which in turn could be related to energy absorption. The complexity of the situation was therefore reduced to calculation of changes in the elastic stiffnesses at all points in the lattice caused by the strain field of a moving dislocation, and concurrently to find for each an appropriate relaxation time. This has not yet been done on a formal basis, and a critical comparison with experimental results awaits this derivation.

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## APPENDIX A

RISE AND DECAY OF THE TORSIONAL WAVE

In the discussion to follow, and in Appendix B, it is assumed that the steady-state elastic stresses and strains in the isotropic loading rod (gage bar and bonding agent) may deviate from that of pure torsion because of the particular elastic behavior of the (111) axis test crystal. However, in accordance with St. Venant's Principle, one considers that the elastic state decays to the pure torsional case at the height of the strain gages (Fig. 2).

With reference to Fig. 3a, a description of the torsional wave can be given. At time $t_{1}$, the wavefront arrives at the strain gages. Less than 2 microseconds are required to attain the maximum torque. The round-trip travel time of the wave between the strain gages and the bond is $\left(t_{2}-t_{1}\right)$. The sharp drop at this time represents wave reflection from the soft bonding agent. At time $t_{3}$, the wave has built up across the bond to its maximum value. The decreasing height between $t_{3}$ and $t_{4}$, the so-called steady state region, represents a small dissipation of torque from plastic deformation in the test crystal. The round-trip travel time of the wave in the test crystal is approximately equal to $\left(t_{4}-t_{2}\right)$, while $\left(t_{5}-t_{4}\right)$ is the time required for the wave reflected from the free end of the test crystal to decay through the bond. Note that the rise time of the wave has increased from 2 to more than 4 microseconds after two passes through the soft bonding agent.

The torque record of Fig. 3a can be constructed mathematically with knowledge of the elastic properties of the bonding agent,
the bond thickness, and the acoustic mismatch between the gage bar and test crystal. Conversely, the elastic properties of the bonding agent can be determined from the torque record for a polycrystalline copper cylinder acoustically matching the gage bar, allied with the proper mathematical equations. With knowledge of the elastic properties of the bonding agent and the bond width, the torque at the surface of the test crystal can be found as a function of time for any test. The reader is referred to Appendix B, Gorman (1968) for a mathematical discussion of the transfer of energy across the bond. The precise calculation of the torque record for the test crystal requires numerical solution by machine techniques. In Fig. 3b, such a solution for the torque record of Fig. 3a is provided.

## APPENDIX B

TORSIONAL STRESSES IN THE TEST CRYSTAL

Because of elastic anisotropy, a pure torsional wave cannot be propagated without dispersion in a $\langle 111\rangle$ direction in copper. Hence, the torsional stresses and displacements of the incident wave cannot be simultaneously realized at the surface of a test crystal, and some type of wave dispersion must follow.

A second, and as will be apparent, more critical problem is the elastic shear modulus defect due to the presence of grown-in dislocations in the test crystal. Koehler and deWit (1959) have treated this effect in detail for fcc crystals. They showed that the shear modulus of copper can be reduced by several percent for small dislocation strains. The effect is much more pronounced for this experiment, as dislocations strains are no longer small. Indeed, using the analysis of deWit and Koehler (1959), a stress less than $1.2 \times 10^{6}$ dynes $/ \mathrm{cm}^{2}$ is required to bow out into the Frank-Read configuration an edge dislocation initially 0.01 cm long.

The shear modulus relating applied stress to dislocation strain decreases by a factor greater than 5 from the low stress to the high stress range. One can write:

$$
\begin{equation*}
\delta S_{e}+\delta S_{d}=\frac{\delta \tau}{\mu_{e f f}} \tag{B-1}
\end{equation*}
$$

where $\delta S_{e}$ is a change in elastic strain, $\delta S_{d}$ is a change in dislocation strain, $\mu_{e f f}$ is the effective shear modulus, and $\delta \tau$ is the corresponding change in applied stress. If $\mu_{0}$ is the perfect crystal shear modulus and $\mu^{\prime}$ is the modulus relating stress to dislocation strain, then:

$$
\begin{equation*}
\frac{\delta \tau}{\mu_{0}}+\frac{\delta \tau}{\mu^{\prime}}=\frac{\delta \tau}{\mu_{\mathrm{eff}}} \tag{B-2}
\end{equation*}
$$

and the modulus defect $\delta \mu / \mu_{0}$ is given by:

$$
\begin{equation*}
\frac{\mu_{o}-\mu_{\text {eff }}}{\mu_{o}}=\frac{\mu_{0}}{\mu^{\prime}+\mu_{0}} . \tag{B-3}
\end{equation*}
$$

In the low stress range, say,

$$
\begin{equation*}
\delta \mu / \mu_{0}=0.04 \tag{B-4}
\end{equation*}
$$

then

$$
\begin{equation*}
\mu^{\prime}=24 \mu_{0} . \tag{B-5}
\end{equation*}
$$

In the high stress range,

$$
\begin{equation*}
\mu^{\prime} \simeq 5 \mu_{0}, \tag{B-6}
\end{equation*}
$$

and

$$
\begin{equation*}
\delta_{\mu} / \mu_{0} \simeq 0.17 \tag{B-7}
\end{equation*}
$$

Quite obviously, the modulus defect will increase with distance from the cylindrical axis of a crystal.

The torque record (Fig. 3a) indicates significant reflection of the incident torsion wave at the crystal surface (time $t_{2}$ ). The acoustic mismatch can be attributed to a combination of the effects discussed above. The modulus defect from dislocation strain, for any test crystal, increases with increasing applied torque. Due to this, the fraction of incident torque reflected must increase for incident waves larger in magnitude. However, one would expect the fraction of the incident torsional wave reflected because of elastic anisotropy to remain independent of the strength of the incident wave if the two effects do not interact strongly. The relative importance of the two effects was determined through two torsion tests with different applied torques on the same crystal. The results are summarized
in Table 5.

## TABLE 5. Fraction of Incident Torsional Wave Reflected at the Surface of a Test Crystal and Magnitude of the Effective Wave Velocity in the Crystal, for Two Wave Strengths.

| Test <br> No. | Maximum Torque <br> $\left(10^{6} \mathrm{~d}\right.$ yne -cm$)$ | Fraction of Incident <br> Wave Reflected | Effective Wave <br> Velocity <br> $10^{5} \mathrm{~cm} \mathrm{sec}^{-1}$ |
| :--- | :---: | :---: | :---: |
| 1 | 12.3 | 0.18 | 1.65 |
| 2 | 3.7 | 0.08 | 1.92 |

Table 5 implies that the modulus defect is the main source of acoustic mismatch. The effective wave velocity in the test crystal is defined as the velocity with which the main body of the torsional wave traverses the crystal. It is given by the length of the crystal divided by the round-trip travel time $\left(t_{4}-t_{2}\right)$ in Fig. 3a. In accord with the modulus defect, this velocity decreases as torque increases.

It remains to determine the state of stress at the surface of the test crystal, in light of the results above.

The elastic anisotropy of the crystal, when considered alone, does not produce significant reflection of the incident torsional wave at the boundary between the gage bar and crystal. This implies that the moment, about the cylindrical axis, of the shear stresses acting on the crystal surface is equal to the applied torque. However, as mentioned previously, the anisotropy does not permit the realization of both torsional stresses and displacements in the crystal.

There are two limiting cases for the boundary condition on the end surface of the crystal in the steady state:
(a) The is otropic loading rod (gage bar and bonding agent) is
assumed to be extremely compliant. Then the stresses on the end surface of the crystal are purely torsional.
(b) The is otropic loading rod is considered to be extremely rigid. Then the displacements on the end surface of the crystal are purely torsional.

Boundary condition (a) is attractive because it provides for stress-free lateral boundaries, while (b) does not. Case (a) is considered in the following.

An orthogonal coordinate system is defined by:

$$
\begin{equation*}
x_{1}=[11 \overline{2}] ; x_{2}=[\overline{1} 10] ; x_{3}=[111] . \tag{B-8}
\end{equation*}
$$

Then the state of torsional stress in the crystal is:

$$
\begin{align*}
& \mathrm{T}_{4}=-\alpha \mathrm{x}_{1} \\
& \mathrm{~T}_{5}=\alpha \mathrm{x}_{2} \tag{B-9}
\end{align*}
$$

all other $\mathrm{T}_{\mathrm{i}}=0$
which satisfies the stress equations of equilibrium and provides stressfree lateral boundaries. $\alpha$ is a number that depends on the total torque.

The matrix of elastic compliances for the coordinate system of
equation (B-8) is (Head 1964):
$\left(\begin{array}{cccccc}\mathrm{s}_{11} & \mathrm{~s}_{12} & \mathrm{~s}_{13} & 0 & \mathrm{~s}_{15} & 0 \\ \mathrm{~s}_{12} & \mathrm{~s}_{11} & \mathrm{~s}_{13} & 0 & { }^{-s_{15}} & 0 \\ { }^{\mathrm{s}_{13}} & \mathrm{~s}_{13} & \mathrm{~s}_{33} & 0 & 0 & 0 \\ 0 & 0 & 0 & \mathrm{~s}_{44} & 0 & -2 \mathrm{~s}_{15} \\ { }^{\mathrm{s}_{15}} & -\mathrm{s}_{15} & 0 & 0 & \mathrm{~s}_{44} & 0 \\ 0 & 0 & 0 & -2 s_{15} & 0 & \mathrm{~s}_{66}\end{array}\right)$

In terms of the three independent compliances ( $s_{11}^{\prime}, s_{12}^{\prime}, s_{44}^{\prime}$ ) with coordinate axes in the directions of the cubic axes, one finds:

$$
\begin{align*}
& s_{11}=s_{12}^{\prime}-\frac{1}{2} D \\
& s_{33}=s_{11}^{1}-\frac{2}{3} D \\
& s_{12}=s_{11}^{\prime}+\frac{1}{6} D \\
& s_{13}=s_{12}^{\prime}+\frac{1}{3} D  \tag{B-10}\\
& s_{44}=s_{44}^{1}-\frac{4}{3} D \mathrm{D} \\
& s_{66}=s_{44}^{\prime}+\frac{2}{3} D \\
& s_{15}=-\sqrt{2} / 3 D
\end{align*}
$$

where

$$
\begin{equation*}
D=s_{11}^{\prime}-s_{12}^{\prime}-\frac{1}{2} s_{44}^{\prime} . \tag{B-11}
\end{equation*}
$$

The elastic strains follow immediately, and these are expressed in terms of the displacement derivatives, $U_{i, j}$ :

$$
\begin{align*}
& \mathrm{U}_{1,1}=\alpha \mathrm{s}_{15} \mathrm{x}_{2} \\
& \mathrm{U}_{2,2}=-\alpha \mathrm{s}_{15} \mathrm{x}_{2} \\
& \mathrm{U}_{3,3}=0 \\
& \mathrm{U}_{2,3}+\mathrm{U}_{3,2}=-\alpha \mathrm{s}_{44} \mathrm{x}_{1}  \tag{B-12}\\
& \mathrm{U}_{1,3}+\mathrm{U}_{3,1}=\alpha \mathrm{s}_{44} \mathrm{x}_{2} \\
& \mathrm{U}_{1,2}+\mathrm{u}_{2,1}={ }^{\alpha s_{1}}{ }_{15} \mathrm{x}_{1}
\end{align*}
$$

The displacements are found by integrating equations ( $B-12$ ), and, neglecting rigid body motion, they are:

$$
\begin{align*}
& \mathrm{U}_{1}=\left\{\alpha \mathrm{s}_{15} \mathrm{x}_{1} \mathrm{x}_{2}\right\}+\alpha \mathrm{s}_{44} \mathrm{x}_{2} \mathrm{x}_{3} \\
& \mathrm{U}_{2}=\left\{\frac{\alpha \mathrm{s}_{15}\left(\mathrm{x}_{1}^{2}-\mathrm{x}_{2}^{2}\right)}{2}\right\}-\alpha \mathrm{s}_{44} \mathrm{x}_{1} \mathrm{x}_{3}  \tag{B-13}\\
& \mathrm{U}_{3}=0
\end{align*}
$$

The non-torsion displacements are emphasized by the curly brackets. Of course, this is not the exact solution to the problem posed in the present experiment because the loading rod is not infinitely compliant. One can, however, obtain a measure of the maximum deviation of the stresses from the pure torsion state by considering that the nontorsional displacements are accommodated entirely in the bonding agent. These can be considered to increase from zero, at the gage bar, to the values given in the curly brackets, at the crystal surface. If $L$ is the bond thickness, then the average strains in the bonding agent due to the anisotropic effect are:

$$
\begin{align*}
& S_{4}^{\prime}=\frac{\alpha s_{15}\left(x_{1}^{2}-x_{2}^{2}\right)}{21 L} \\
& S_{5}^{\prime}=\frac{\alpha{ }^{s} 15^{x_{1}} x_{2}}{L} \tag{B-14}
\end{align*}
$$

with accompanying stresses:

$$
\begin{align*}
T_{4}^{\prime} & =\frac{\alpha s_{15} \mu\left(x_{1}^{2}-x_{2}^{2}\right)}{2 \mathrm{~L}}  \tag{B-15}\\
T_{5}^{\prime} & =\frac{\alpha s_{15}{ }^{\mu x_{1}} x_{2}}{L}
\end{align*}
$$

where $\mu$ is the shear modulus of the bonding agent.
In the worst possible case, the torsional stress state will be deformed by the values of $\mathrm{T}_{4}^{\prime}$ and $\mathrm{T}_{5}^{\prime}$. When compared to the torsional stresses, they are found to be insignificant. Consider:

$$
\begin{equation*}
\left|\frac{\mathrm{T}_{5}^{\prime}}{\mathrm{T}_{5}}\right|=\left|\frac{\mathrm{s}_{15} \mu \mathrm{x}_{1}}{\mathrm{~L}}\right| \tag{B-16}
\end{equation*}
$$

Hearmon (1961) lists the values of the three independent stiffnesses, and for copper:

$$
\begin{equation*}
s_{11}^{\prime}=14.5 ; s_{12}^{\prime}=-6.05 ; s_{44}^{\prime}=14.6 \tag{B-17}
\end{equation*}
$$

in units of $10^{-13} \mathrm{~cm}^{2} /$ dyne. Then, using equation ( $\mathrm{B}-10$ ):

$$
\begin{equation*}
s_{15}=-6.2 \times 10^{-13} \mathrm{~cm}^{2} / \text { dyne } \tag{B-18}
\end{equation*}
$$

Customarily, the bonding agent had characteristics close to the following:

$$
\begin{align*}
& \mu=4 \times 10^{8} \text { dynes } / \mathrm{cm}^{2} \\
& L=5 \times 10^{-3} \mathrm{~cm} \tag{B-19}
\end{align*}
$$

Then the maximum value of $\left|T_{5}^{\prime} / T_{5}\right|$ is found from equations $(B-16)$, (B-18), and (B-19) when $x_{1}=0.67 \mathrm{~cm}$.

$$
\begin{equation*}
\left|\mathrm{T}_{5}^{\prime} / \mathrm{T}_{5}\right|<0.04 \tag{B-20}
\end{equation*}
$$

The elastic inhomogeneity due to the presence of dislocations in the crystal poses a more serious problem than elastic anisotropy. The cylindrical crystal now can be considered as elastically isotropic, but with radially-dependent elastic moduli. Again, one finds the same two limiting conditions on the end boundary as before, but now both satisfy the requirement of a stress-free lateral boundary. In the following, boundary condition (b) is considered. This provides the case for the most severe possible distortion of the stress state.

The coordinate system of equation ( $\mathrm{B}-8$ ) is used, but an isotropic, inhomogeneous shear modulus, $\mu(r)$, is assumed, where $r$ is the distance from the cylindrical axis of the crystal. Then:

$$
\begin{align*}
& \mathrm{U}_{1}=-\beta \mathrm{x}_{2} \mathrm{x}_{3} \\
& \mathrm{U}_{2}=\beta \mathrm{x}_{1} \mathrm{x}_{3}  \tag{B-21}\\
& \mathrm{U}_{3}=0
\end{align*}
$$

where $\beta$ is the angle of twist per unit length. The corresponding strains are:

$$
\begin{align*}
& S_{4}=\beta x_{1}  \tag{B-22}\\
& S_{5}=-\beta x_{2}
\end{align*}
$$

and, using Hooke's law, the elastic stresses are:

$$
\begin{align*}
& \mathrm{T}_{4}^{\prime \prime}=\mu(\mathrm{r}) \beta \mathrm{x}_{1}  \tag{B-23}\\
& \mathrm{~T}_{5}^{\prime \prime}=-\mu(\mathrm{r}) \beta \mathrm{x}_{2}
\end{align*}
$$

To a first approximation, $\mu(r)$ is assumed to decrease linearly with radius. Using equation ( $B-7$ ), it has the form

$$
\begin{equation*}
\mu(r)=\mu_{0}\left(1-0.17 \frac{r}{r_{0}}\right) \tag{B-24}
\end{equation*}
$$

where $r_{o}$ is the outer radius of the crystal. The angle of twist, $\beta$, is found by considering the total torque, $M$, about the cylindrical axis. In terms of cylindrical coordinates $(x, \theta)$ in the $\left(x_{1}, x_{2}\right)$ plane:

$$
\begin{equation*}
M=\int_{r=0}^{r} \int_{\theta=0}^{2 \pi} \mu(r) \beta r^{3} d r d \theta, \tag{B-25}
\end{equation*}
$$

or

$$
\begin{equation*}
\beta=\frac{M}{(0.22) 2 \pi \mu_{0} r_{0}^{4}} \tag{B-26}
\end{equation*}
$$

This stress state can be compared to the homogeneous case for the same total torque $M$. In the latter situation, the stress state is torsional and:

$$
\begin{align*}
& T_{4}=\mu_{0} \beta^{\prime} x_{1}  \tag{B-27}\\
& T_{5}=-\mu_{0} \beta^{\prime} x_{2}
\end{align*}
$$

where

$$
\begin{equation*}
\beta^{\prime}=\frac{M}{(0.25) 2 \pi \mu_{0} r_{o}^{4}} \tag{B-28}
\end{equation*}
$$

The ratio, $T_{4}^{\prime \prime} / T_{4}$, is found with the aid of equations $(B-26)$ and ( $B-28$ ).

$$
\begin{equation*}
\frac{\mathrm{T}_{4}^{\prime \prime}}{\mathrm{T}_{4}}=1.14\left(1-0.17 \frac{\mathrm{r}}{\mathrm{r}_{\mathrm{o}}}\right) \tag{B-29}
\end{equation*}
$$

$\mathrm{T}_{4}^{\prime \prime} / \mathrm{T}_{4}$ decreases linearly from 1.14 at $\mathrm{r}=0$ to 0.945 at $\mathrm{r}=\mathrm{r}_{\mathrm{o}}$. In the present experiment, one would expect the stress distortion to be less than that indicated by equation ( $\mathrm{B}-29$ ), because the loading rod is certainly non-rigid.

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Fig. 1 Typical Scratch Segment Before Testing. (a) Dislocations on Primary Slip Planes with Burgers Vectors $\underline{b}_{1}$ and $\underline{b}_{2}$, (b) the Same Area as in (a) but Etched to Reveal Forest Dislocations.

Fig. 2 Schematic Diagram of Lower End of Torsion Machine.
Fig. 3 Typical Torque vs. Time Record for Torsion Test. (a) at Strain Gages, (b) Calculated Pulse at Test Crystal Surface.

Fig. 4 Typical Scratch Segment. (a) Before Torsion Testing, (b) After Load Application, (c) Same as (b) but Surface Etched to Reveal Forest Dislocations.

Fig. 5 Dislocation Displacement as a Function of Distance $r$ from the Cylindrical Axis of the Test Crystal.

Fig. 6 Dislocation Velocity as a Function of Resolved Shear Stress for the Range of Stresses Used at Each Test Temperature.

Fig. 7 Dislocation Damping Coefficient for Edge Dislocations in Copper Single Crystals as a Function of Temperature (from Linearized Measurements).

Fig. 8 Schematic Representation of a Dislocation Gliding on a Primary Slip Plane Under the Influence of Torsional Stresses.

